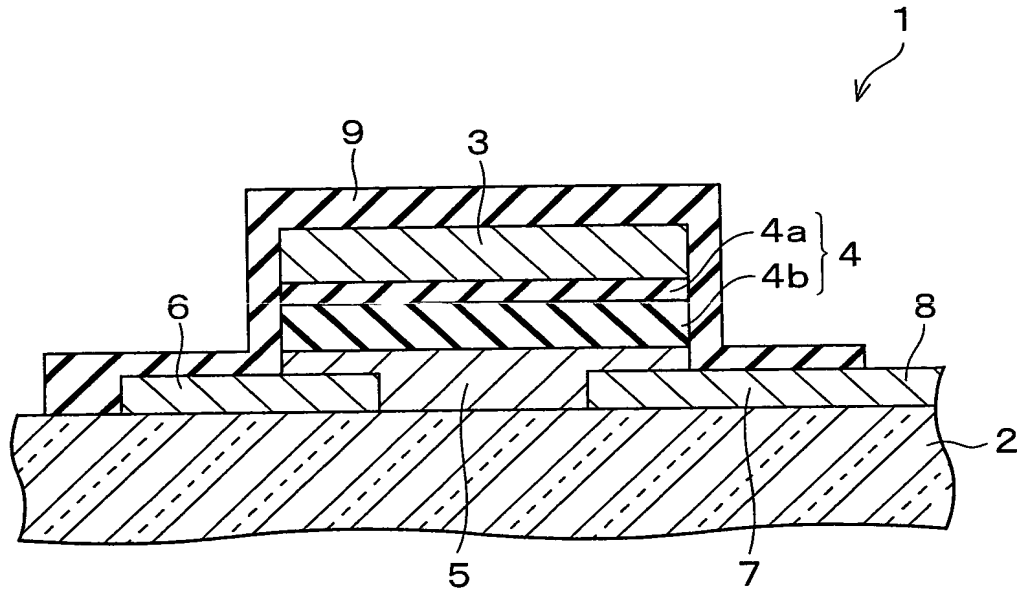


FIG. 1



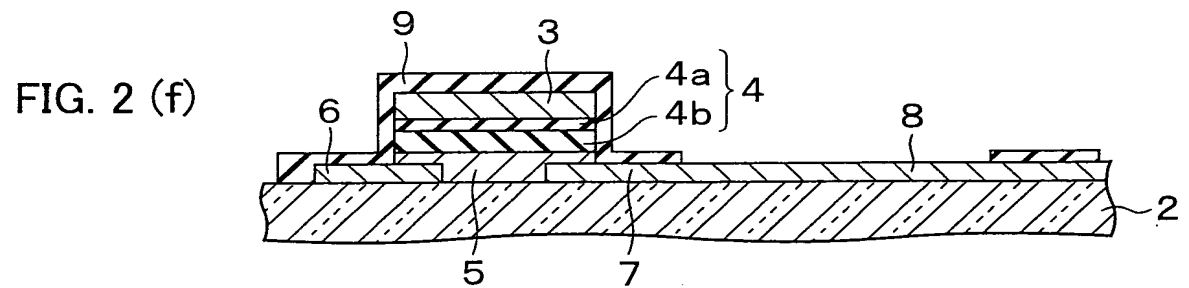
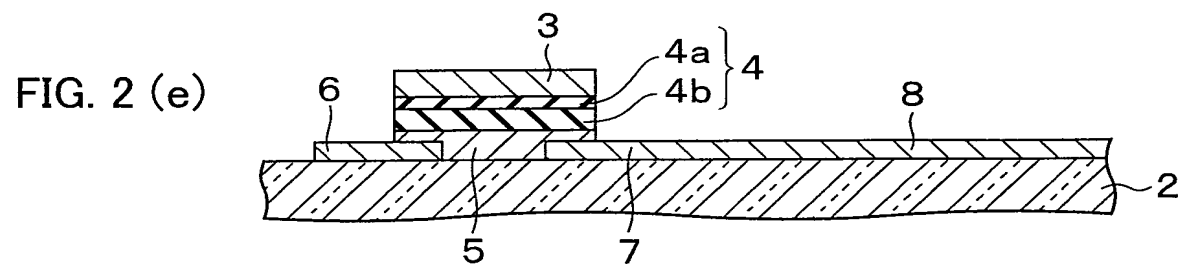
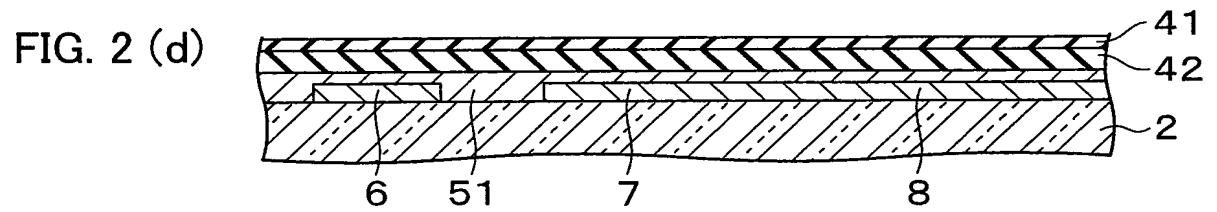
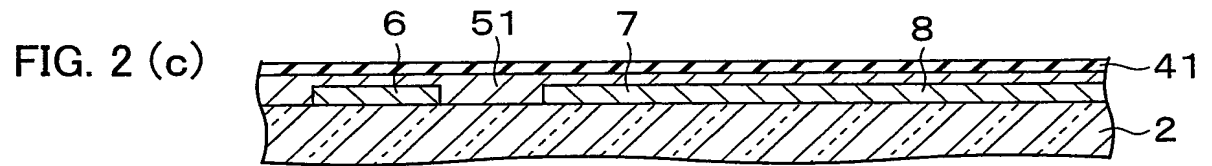
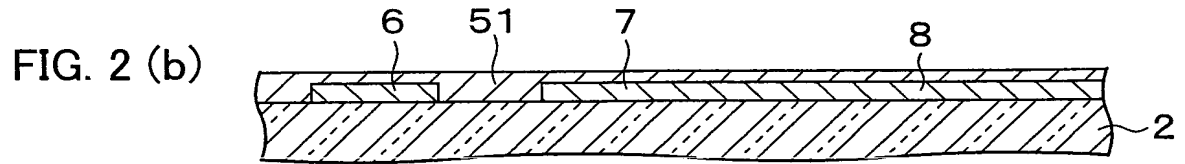
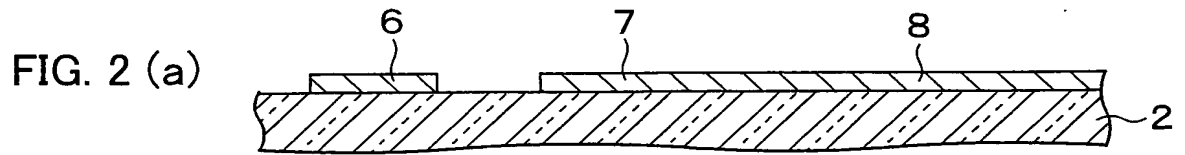


FIG. 3

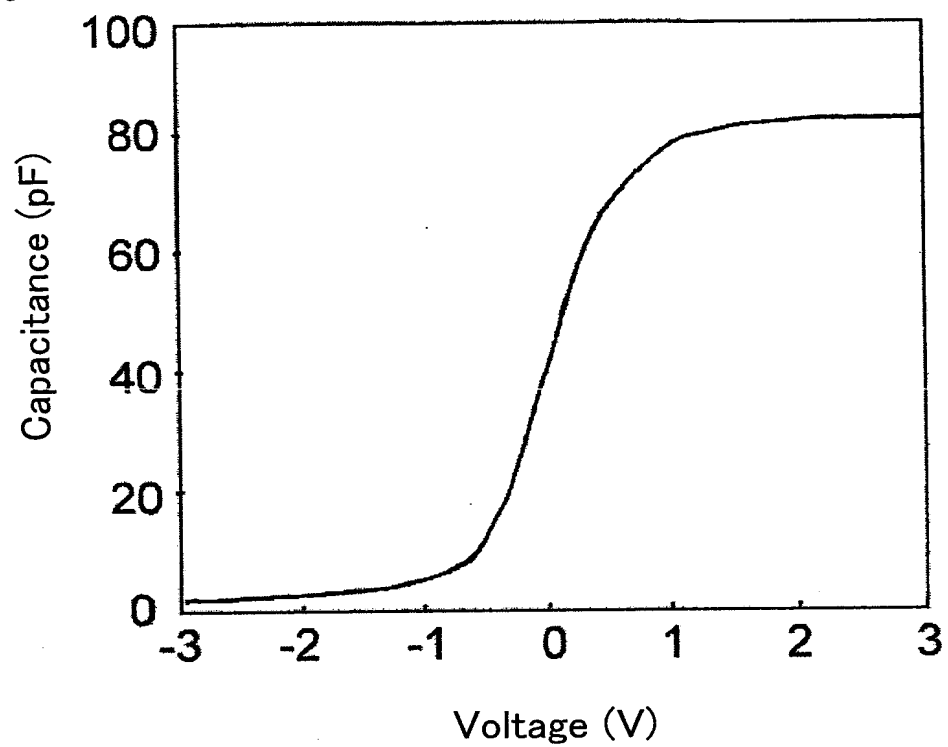


FIG. 4

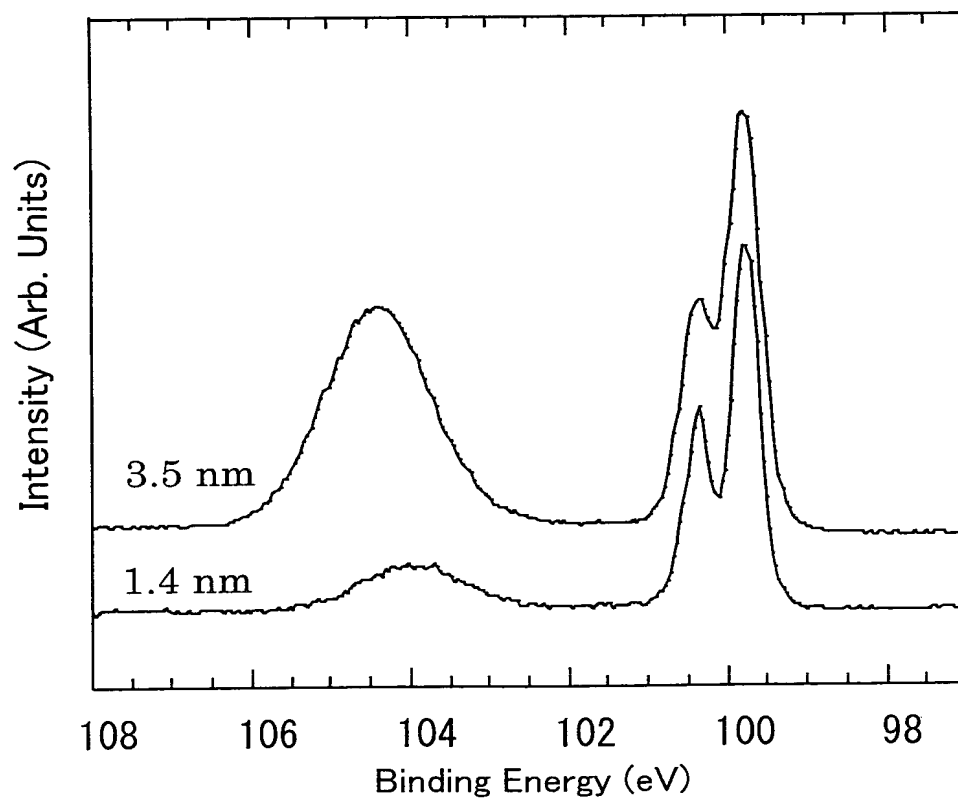


FIG. 5

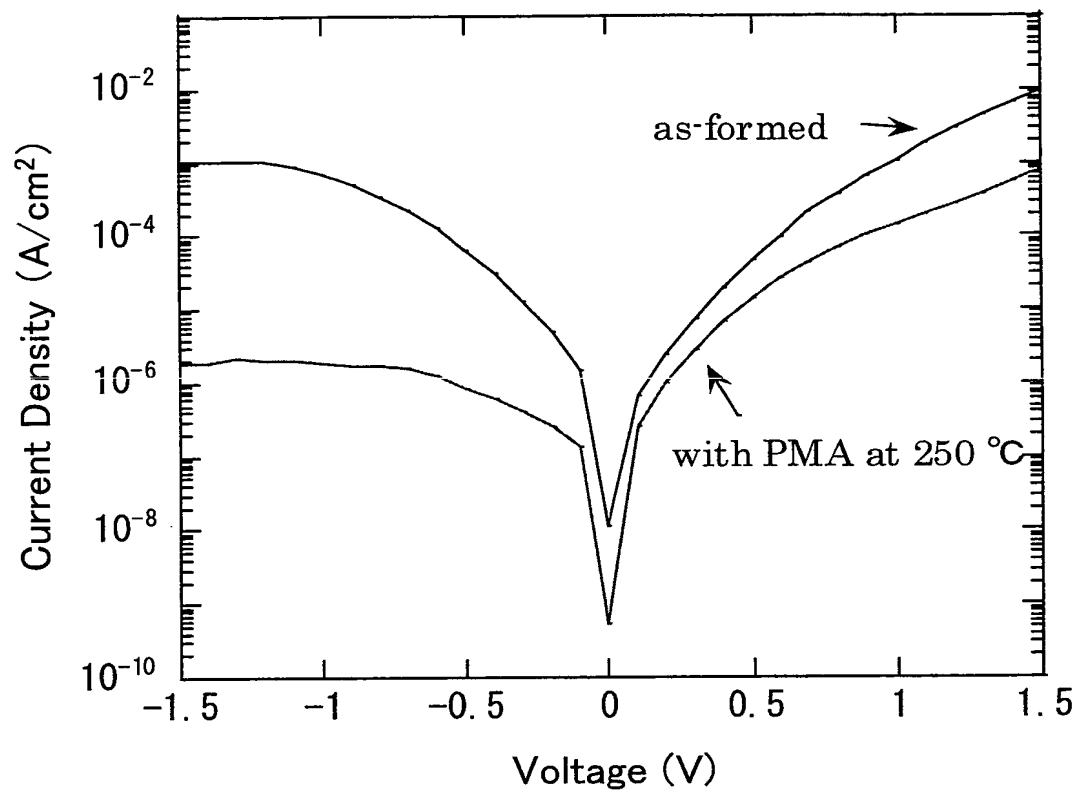


FIG. 6

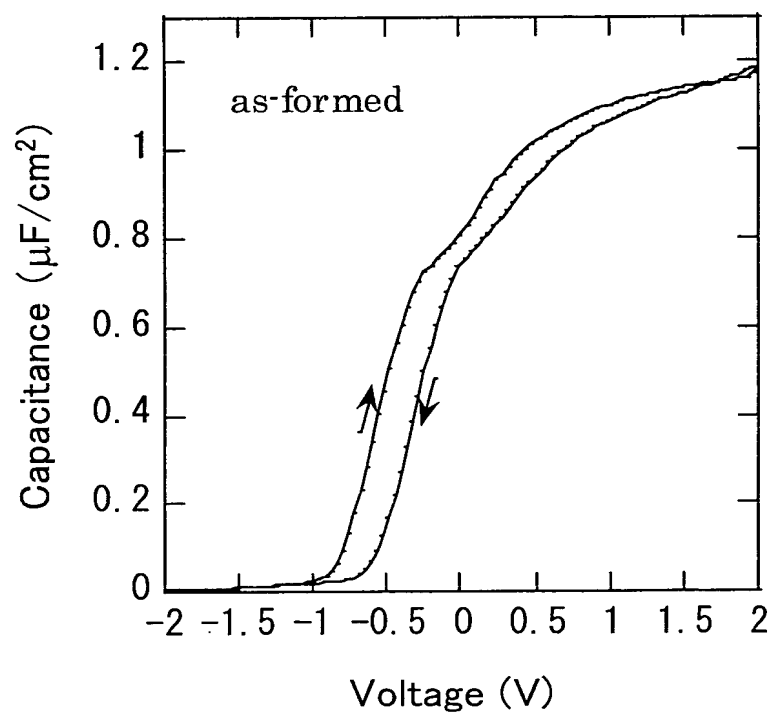


FIG. 7

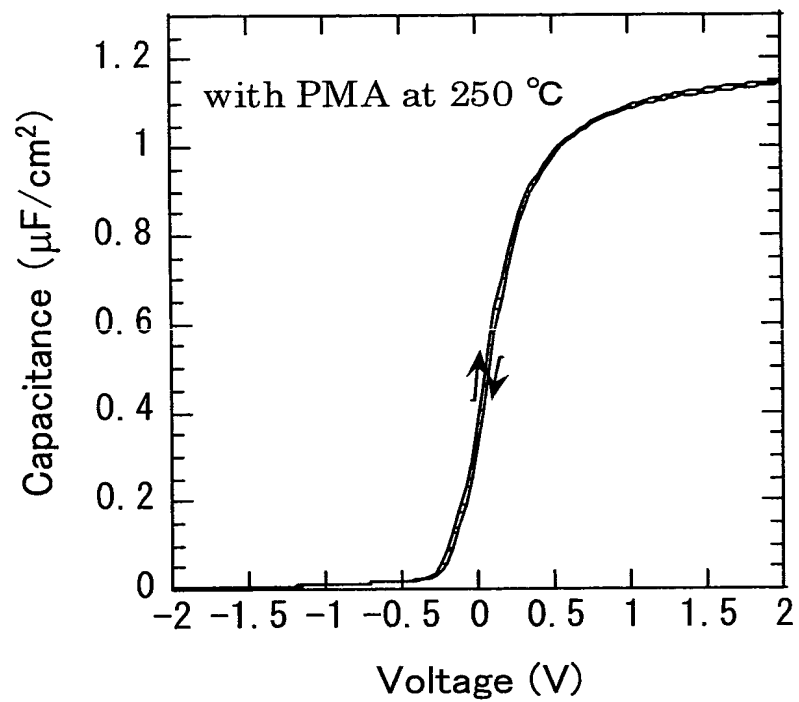


FIG. 8

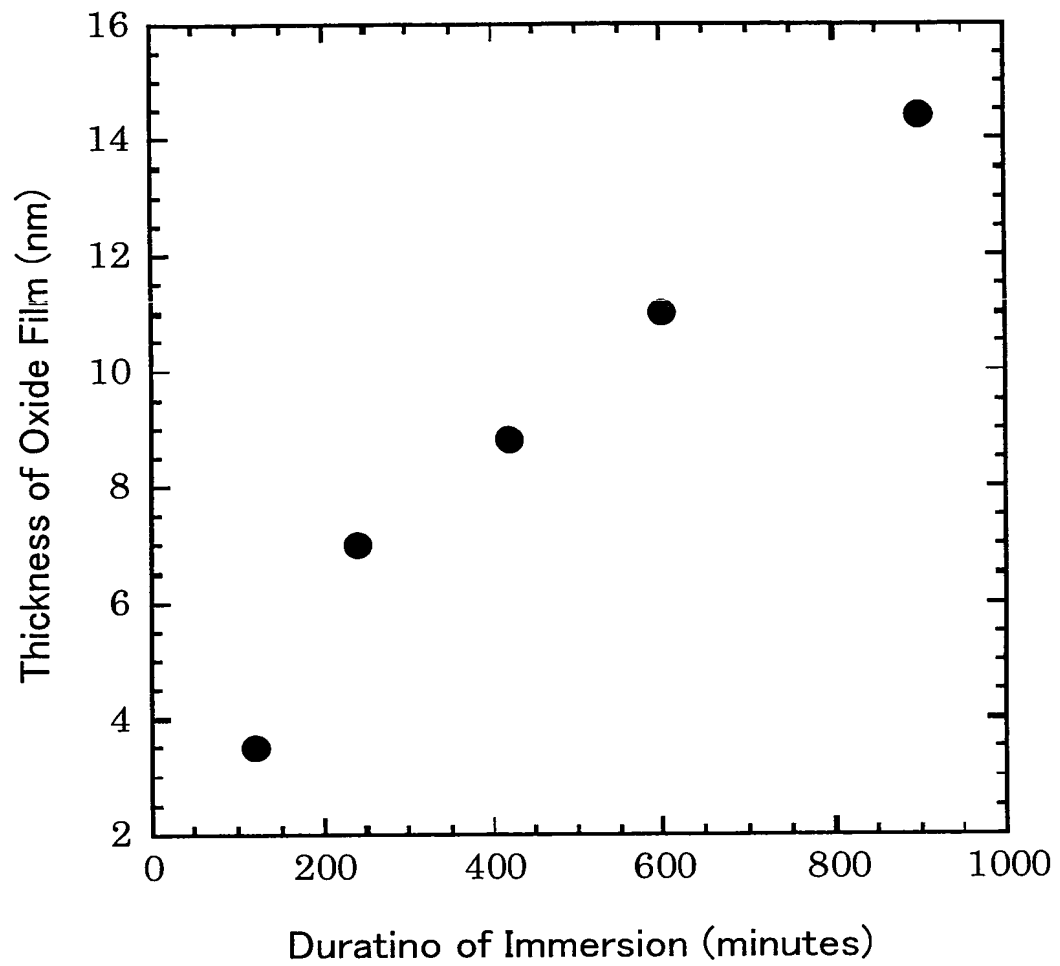


FIG. 9

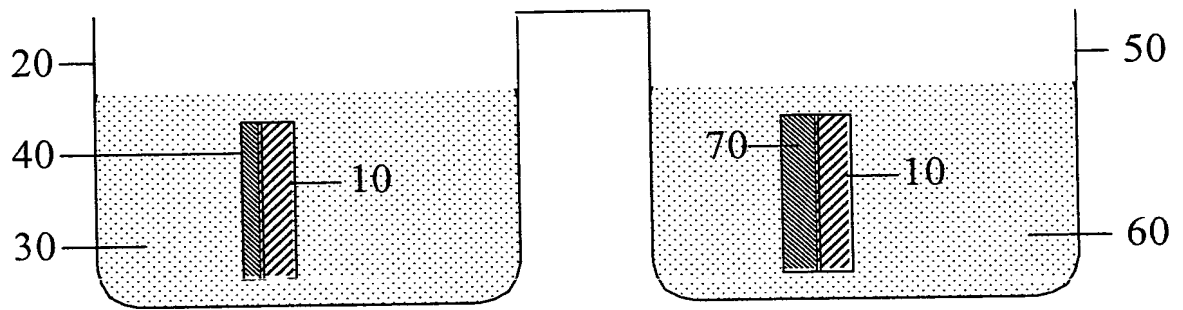


FIG. 10

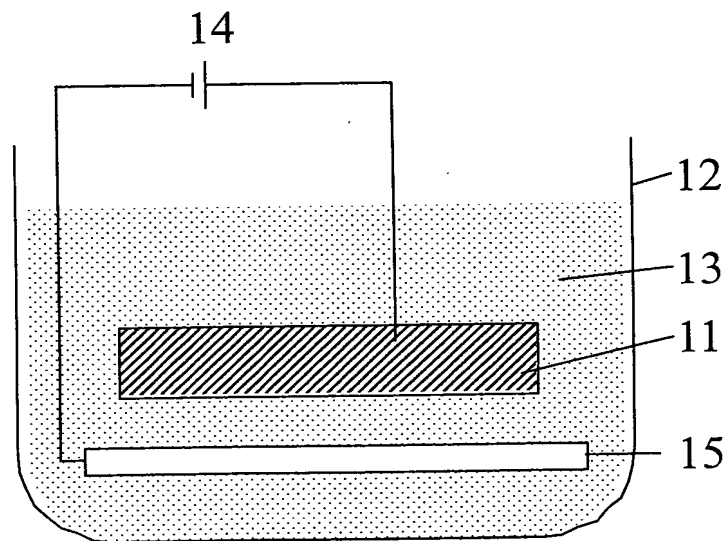


FIG. 11

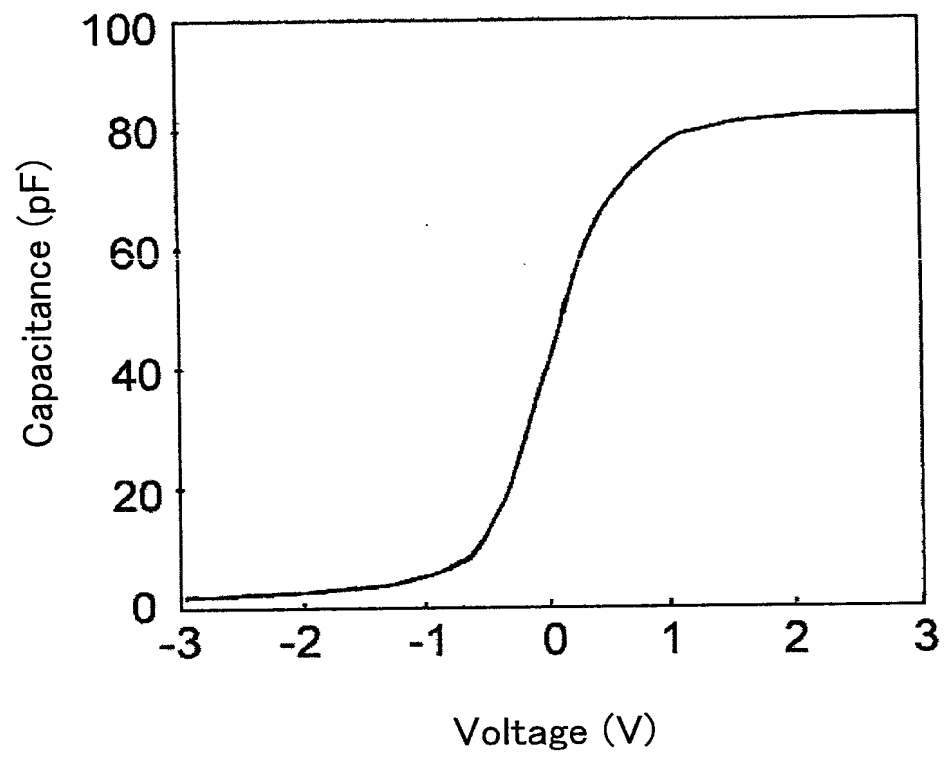
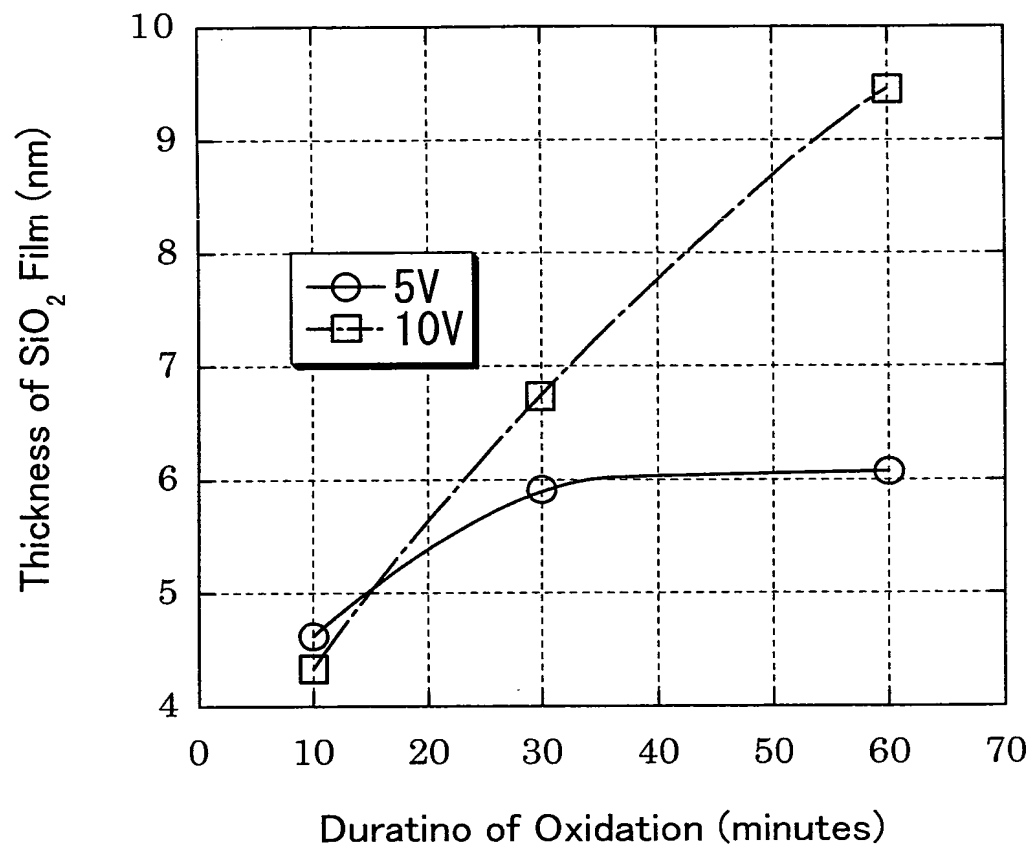


FIG. 12



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FIG. 13

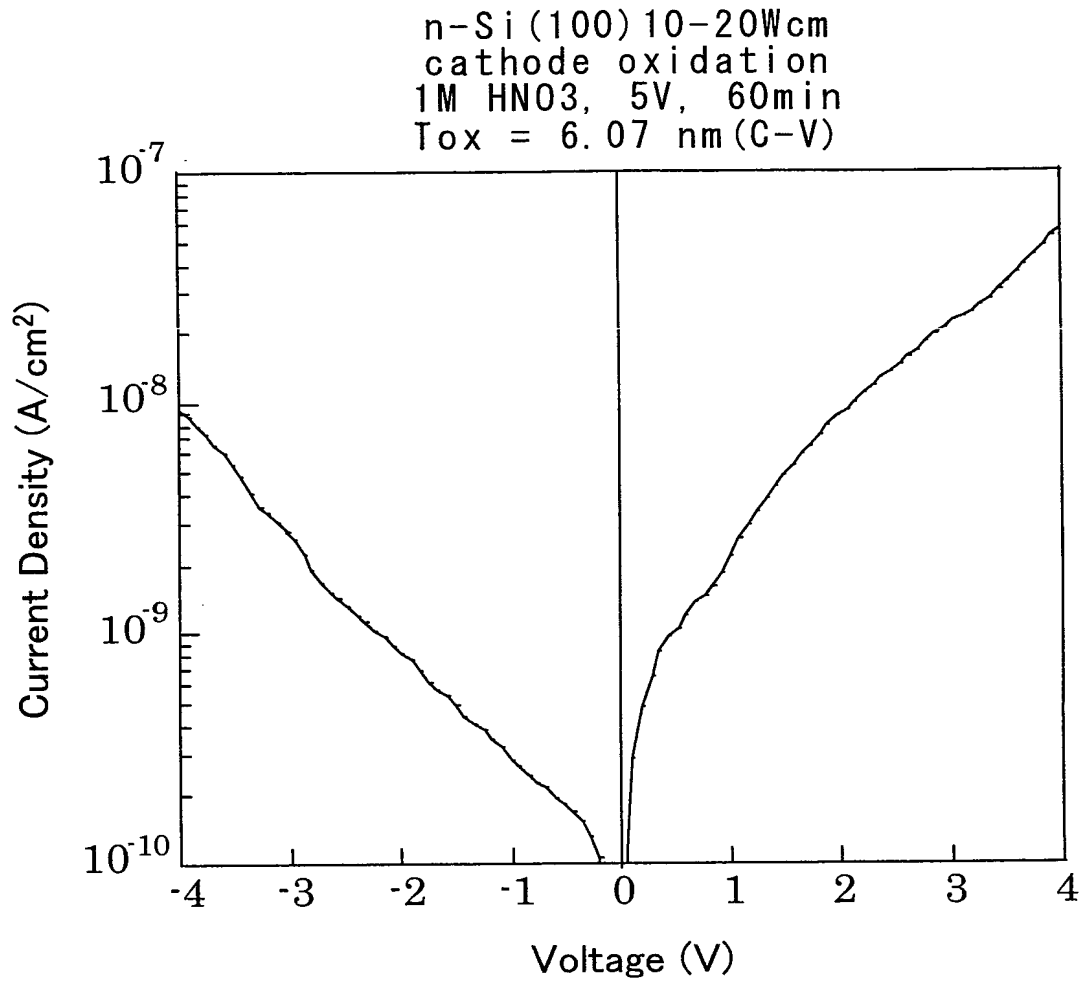
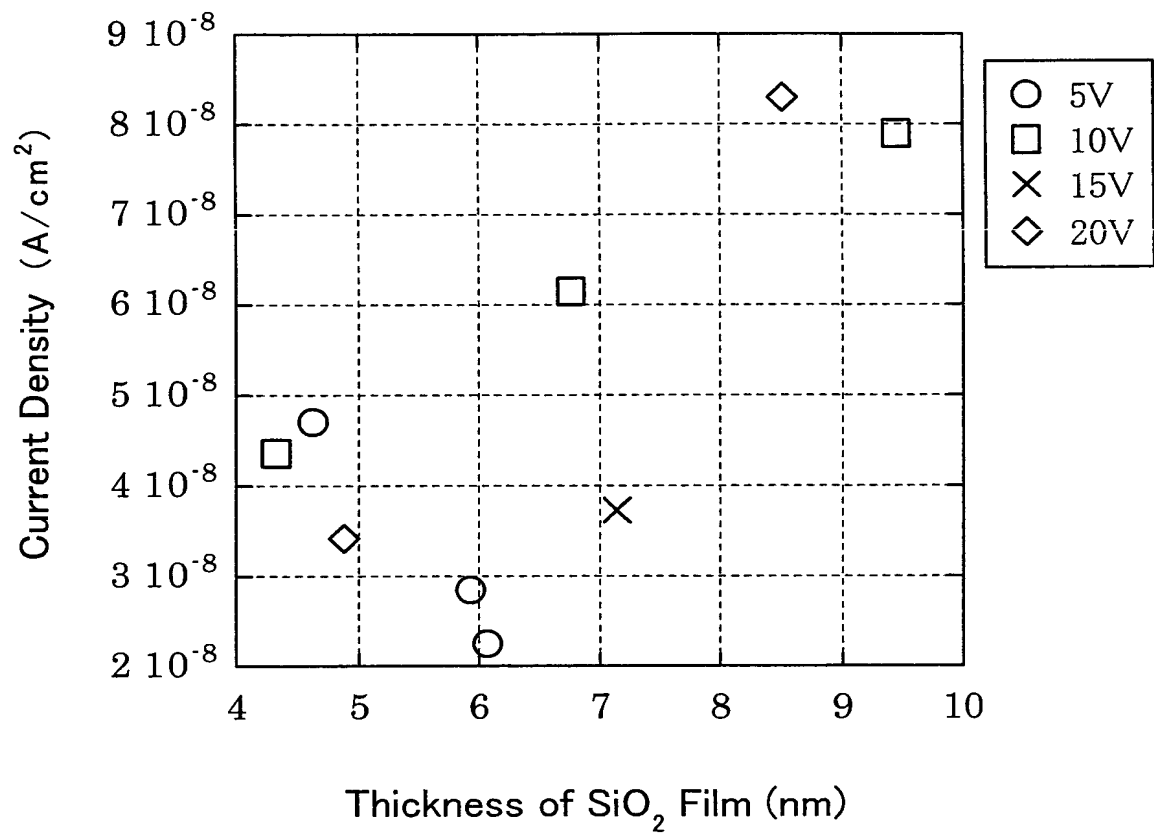


FIG. 14



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FIG. 15

n-Si (100) 10-20 Ω cm
Anodization
0.01M HClO₄ 10V, 10min
 T_{ox} = 8.50 nm (XPS)
6.68 nm (C-V)

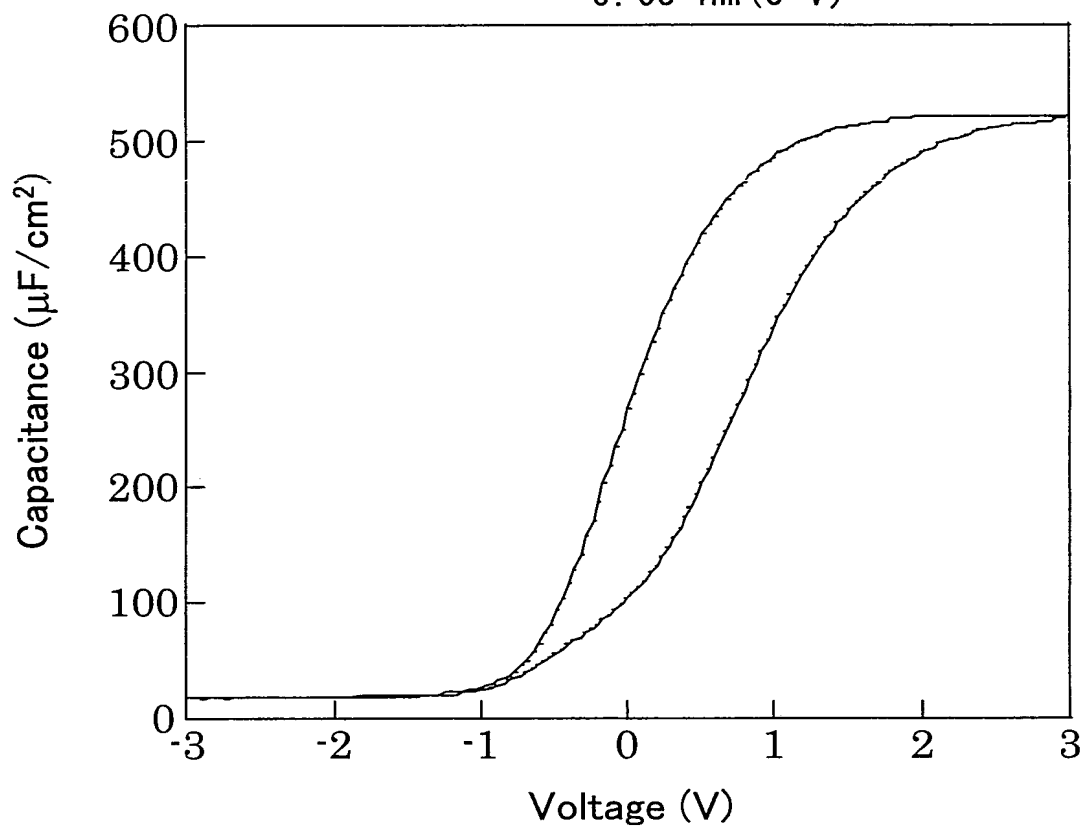


图 16

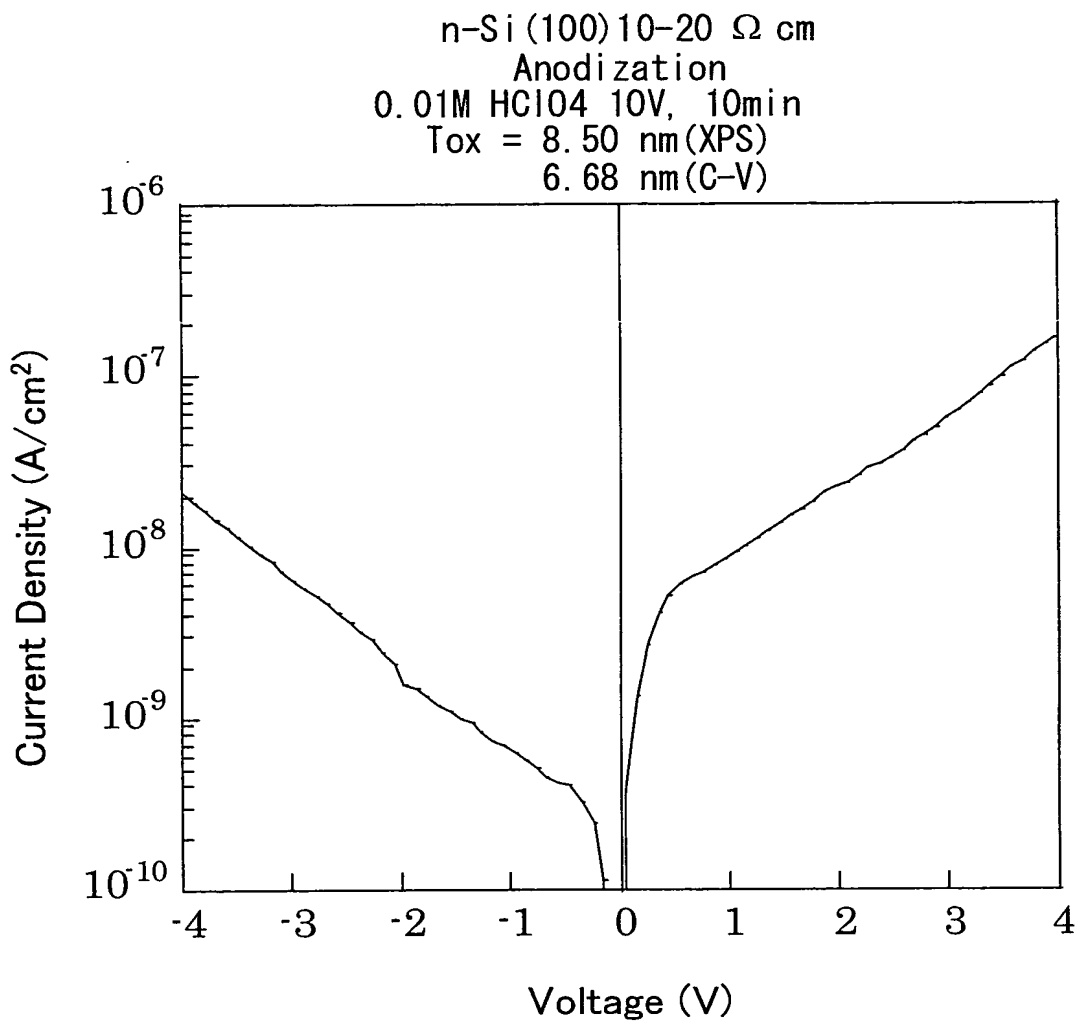


FIG. 17

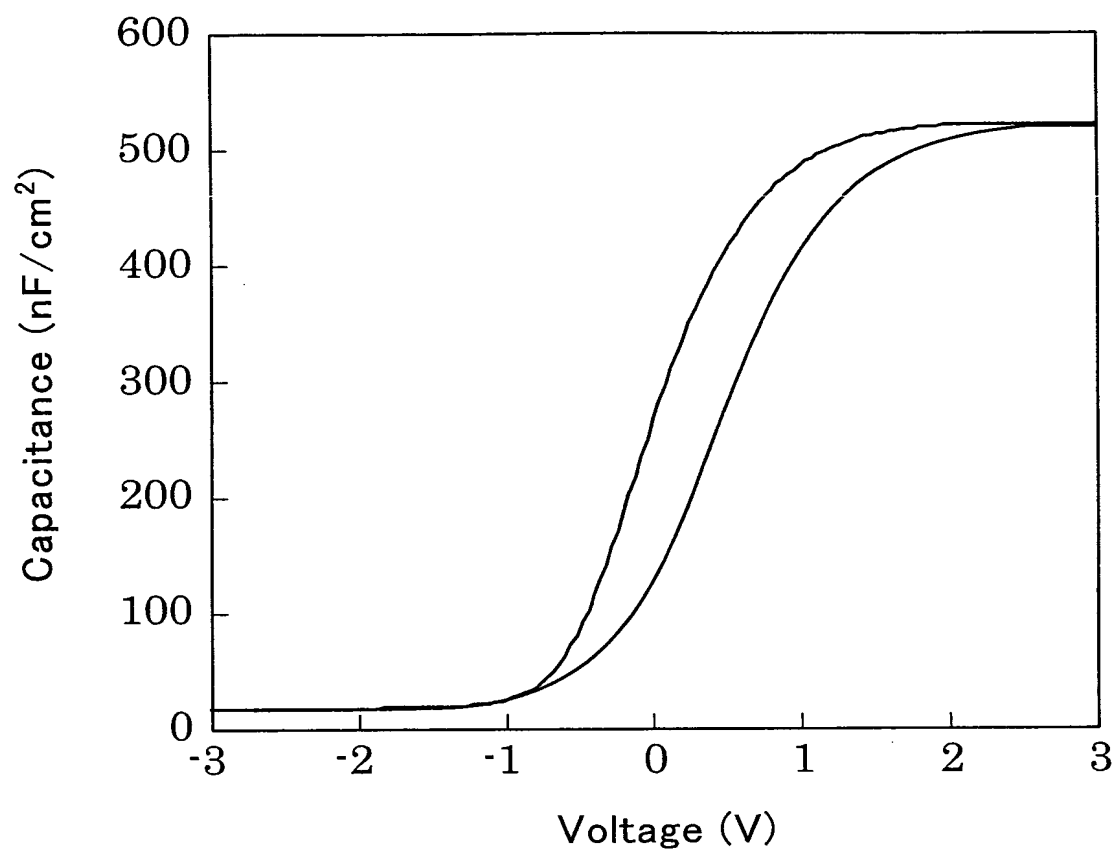


图 18

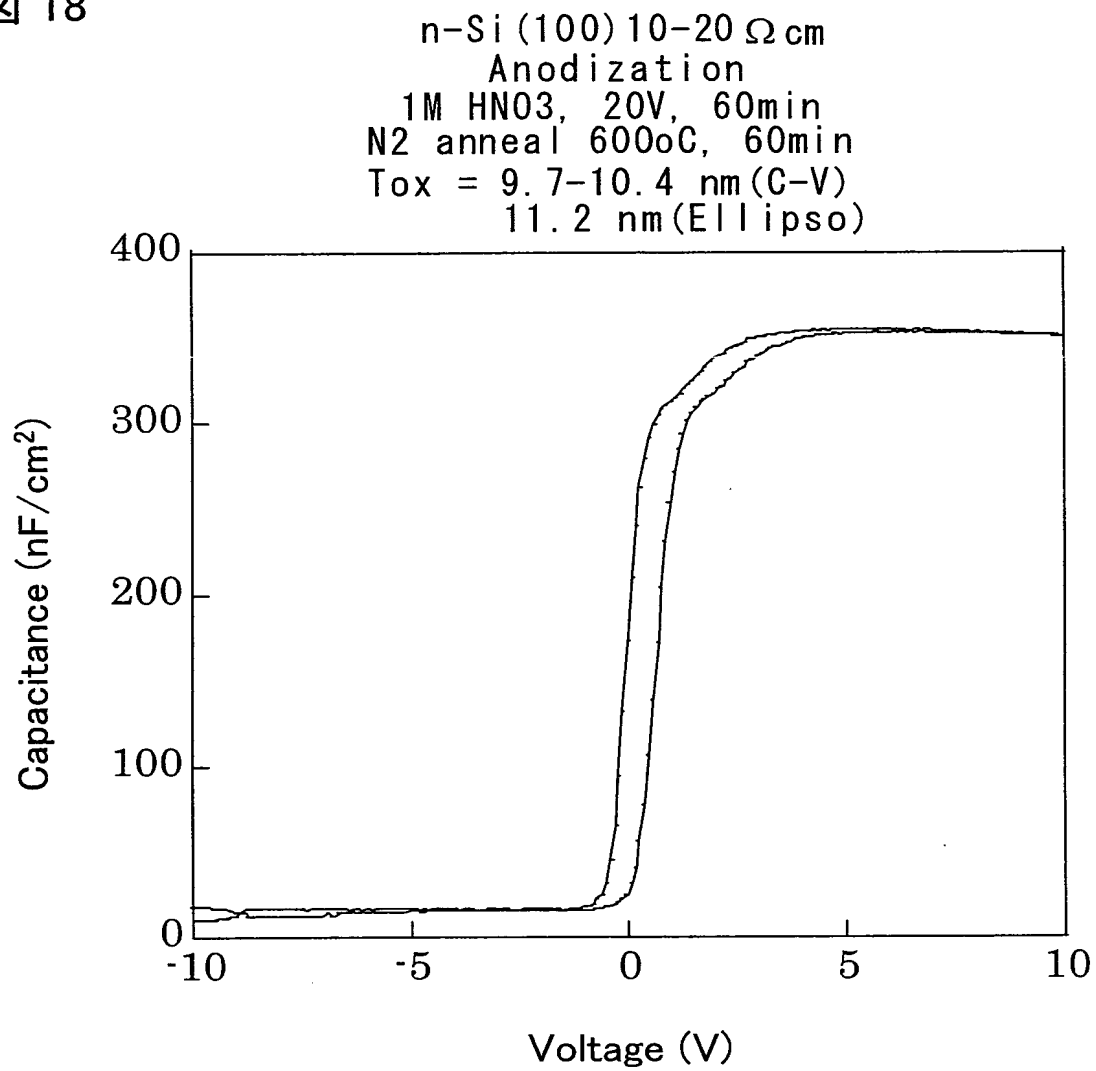


图 19

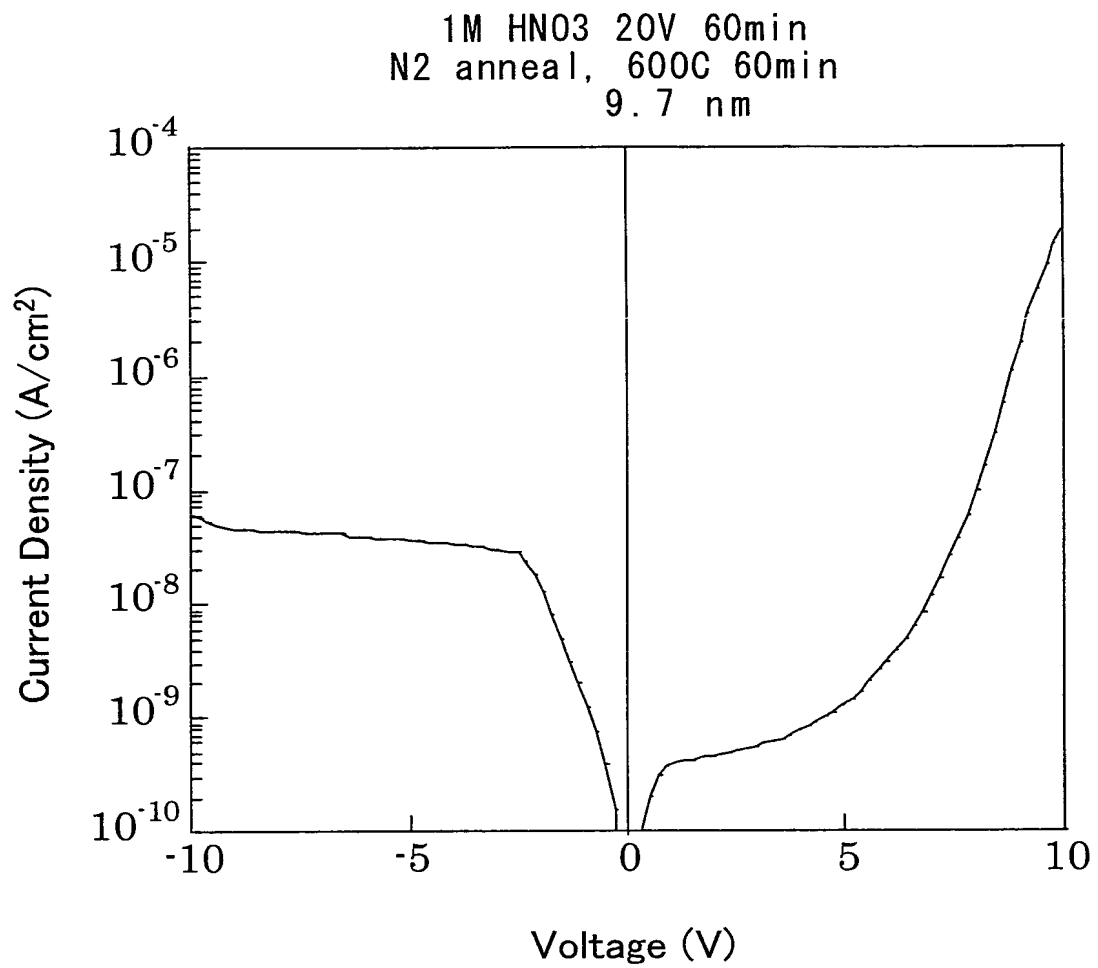
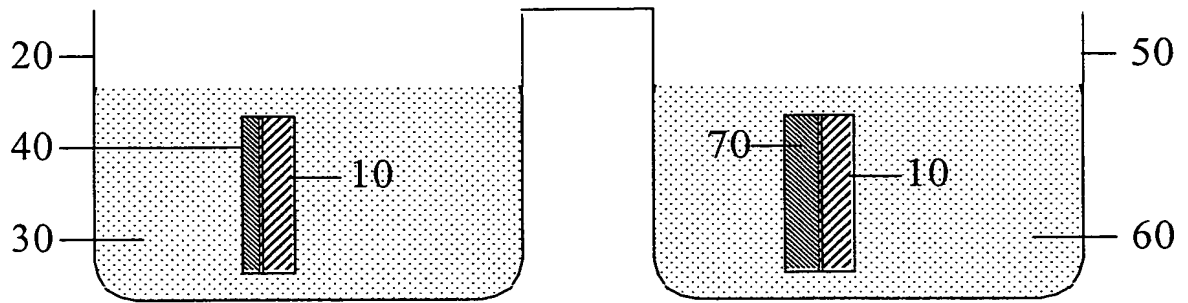


FIG. 21



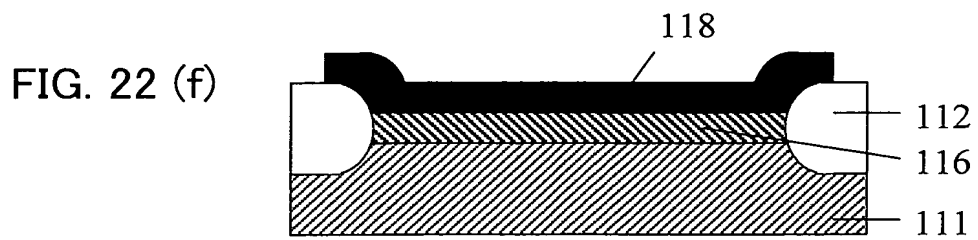
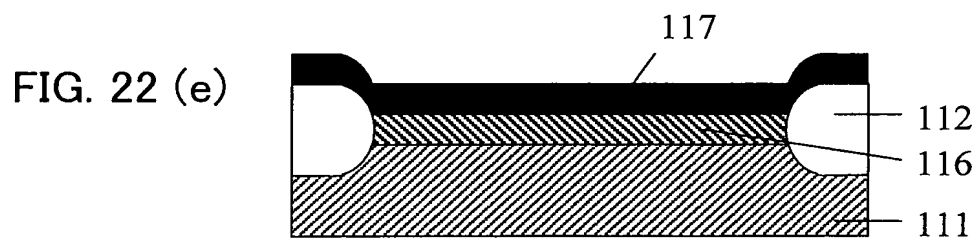
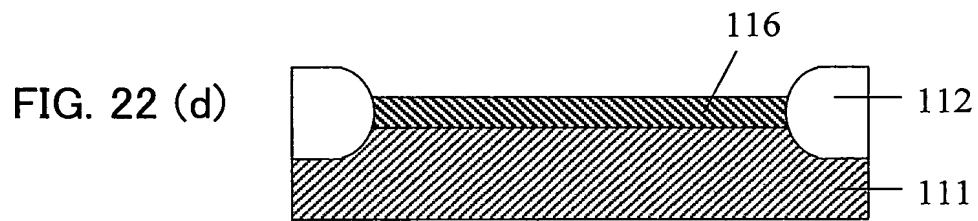
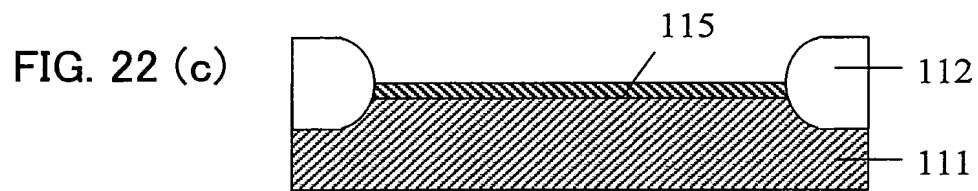
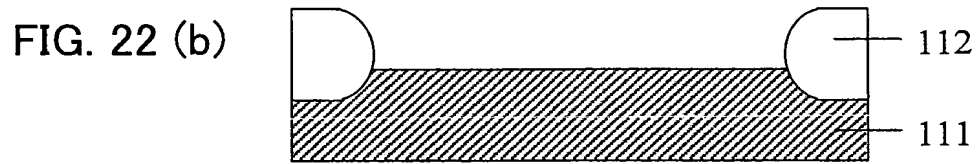
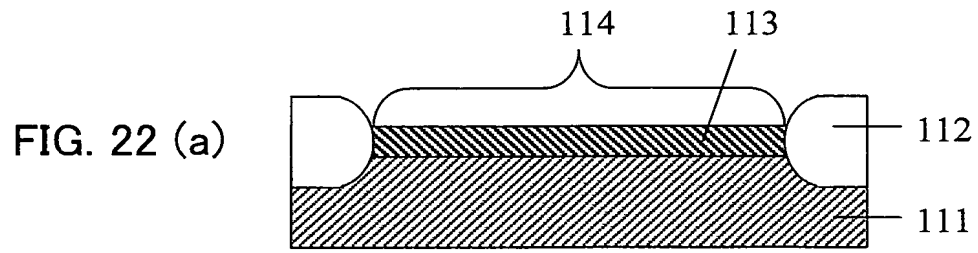


FIG. 23

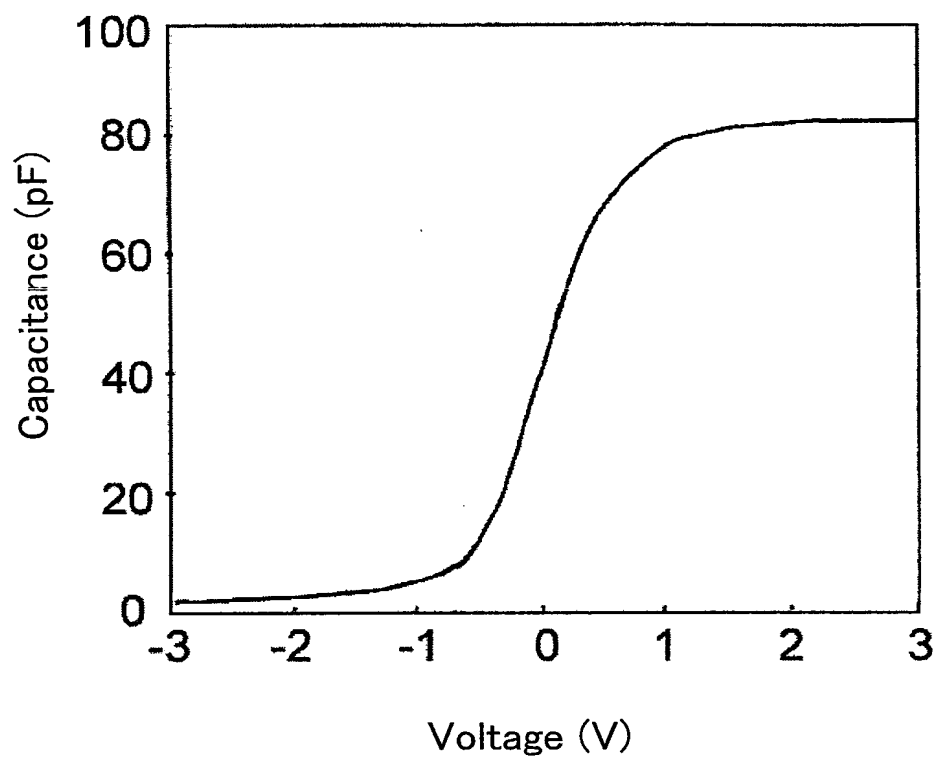


FIG. 24

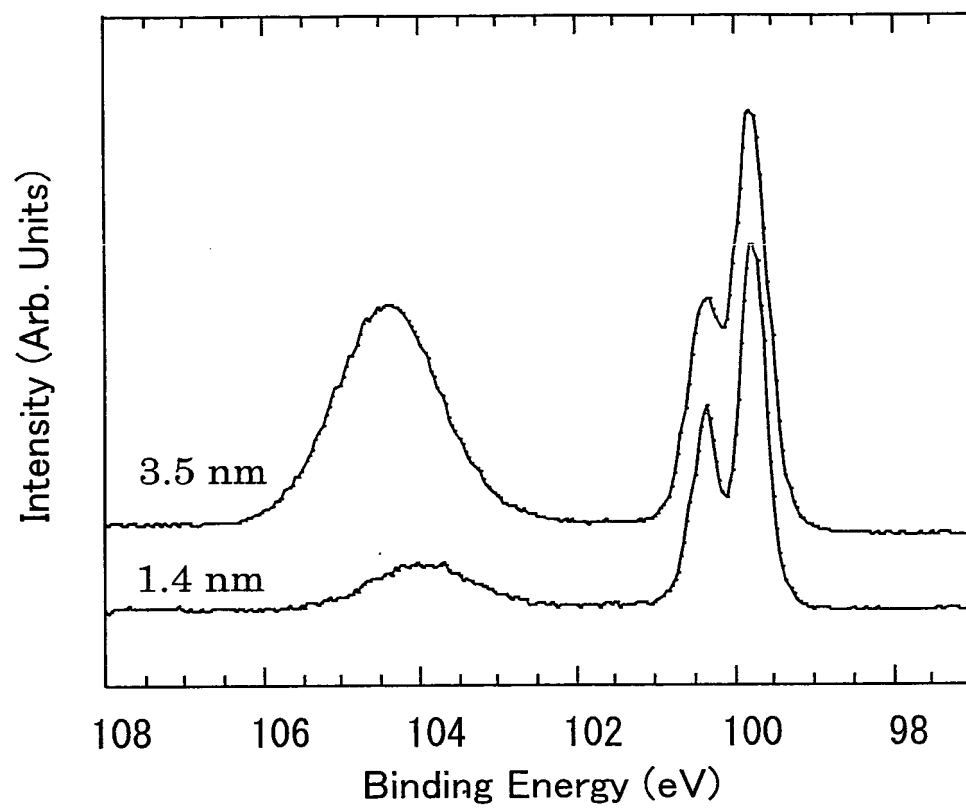


FIG. 25

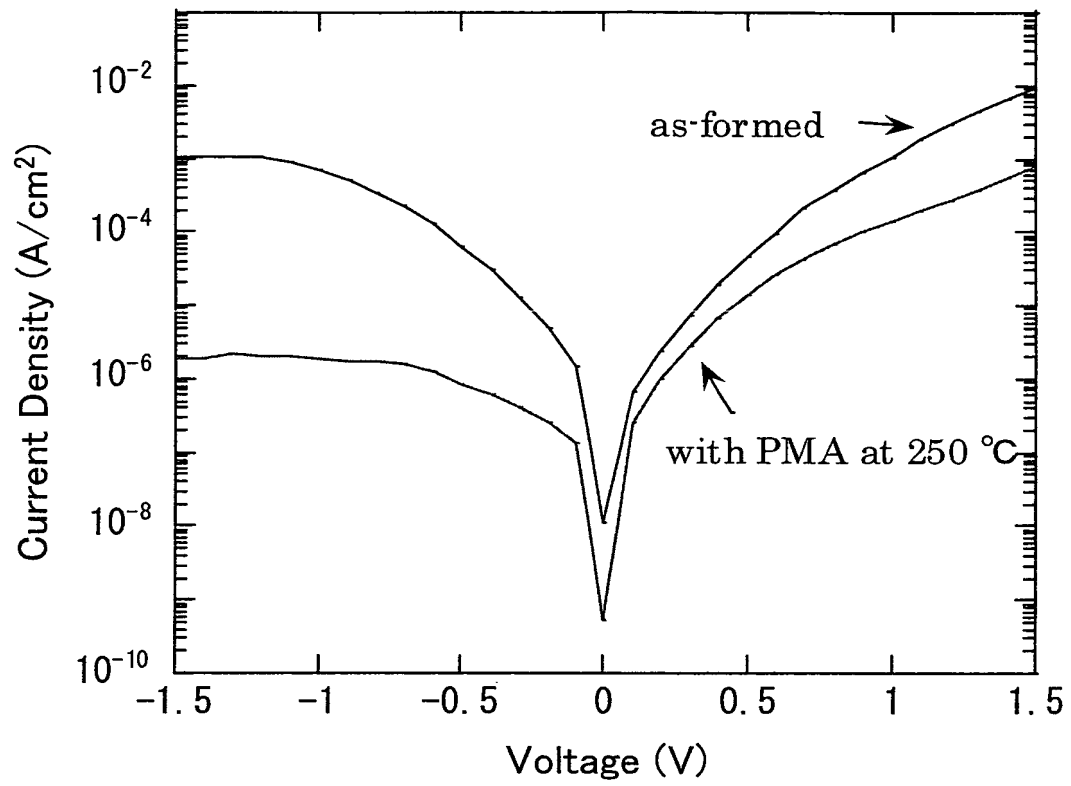


FIG. 26

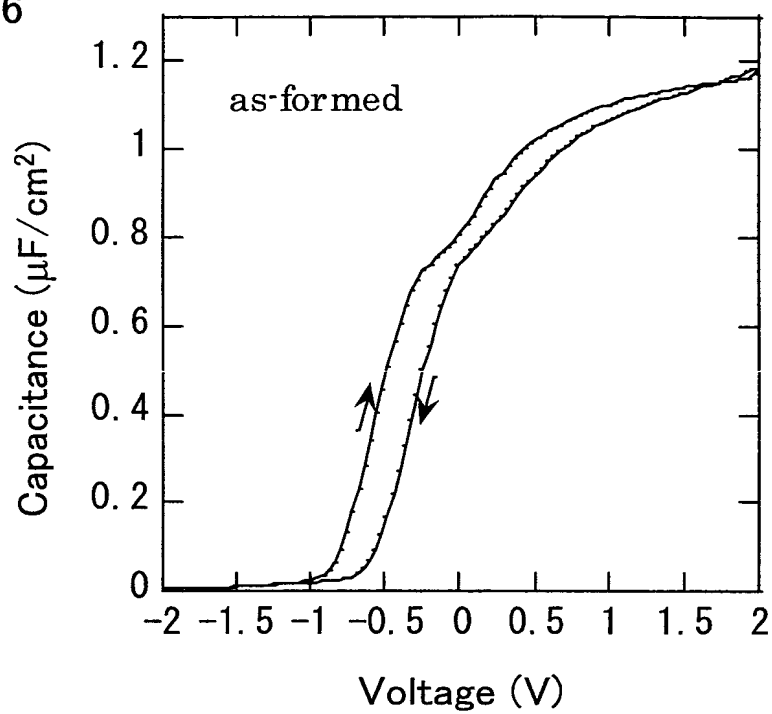


FIG. 27

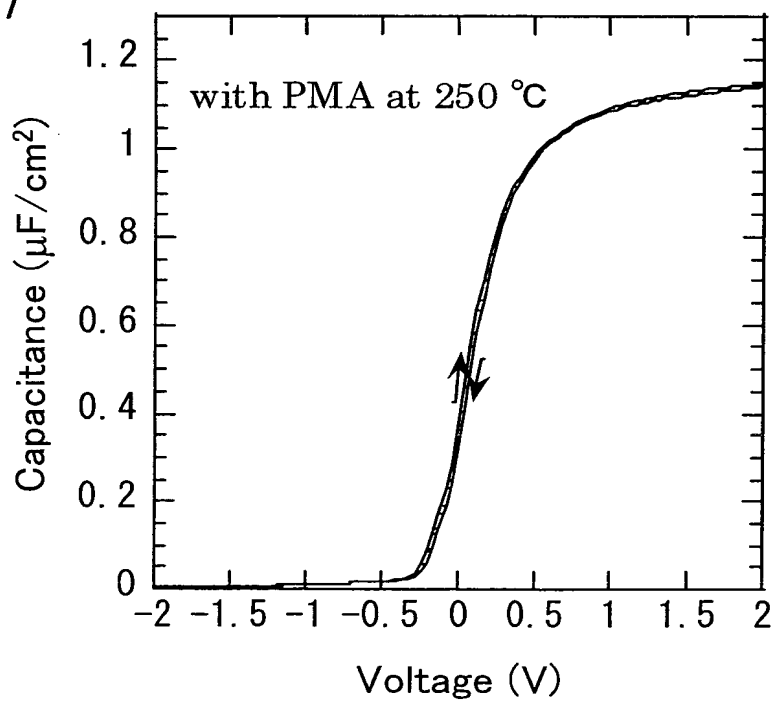


FIG. 28

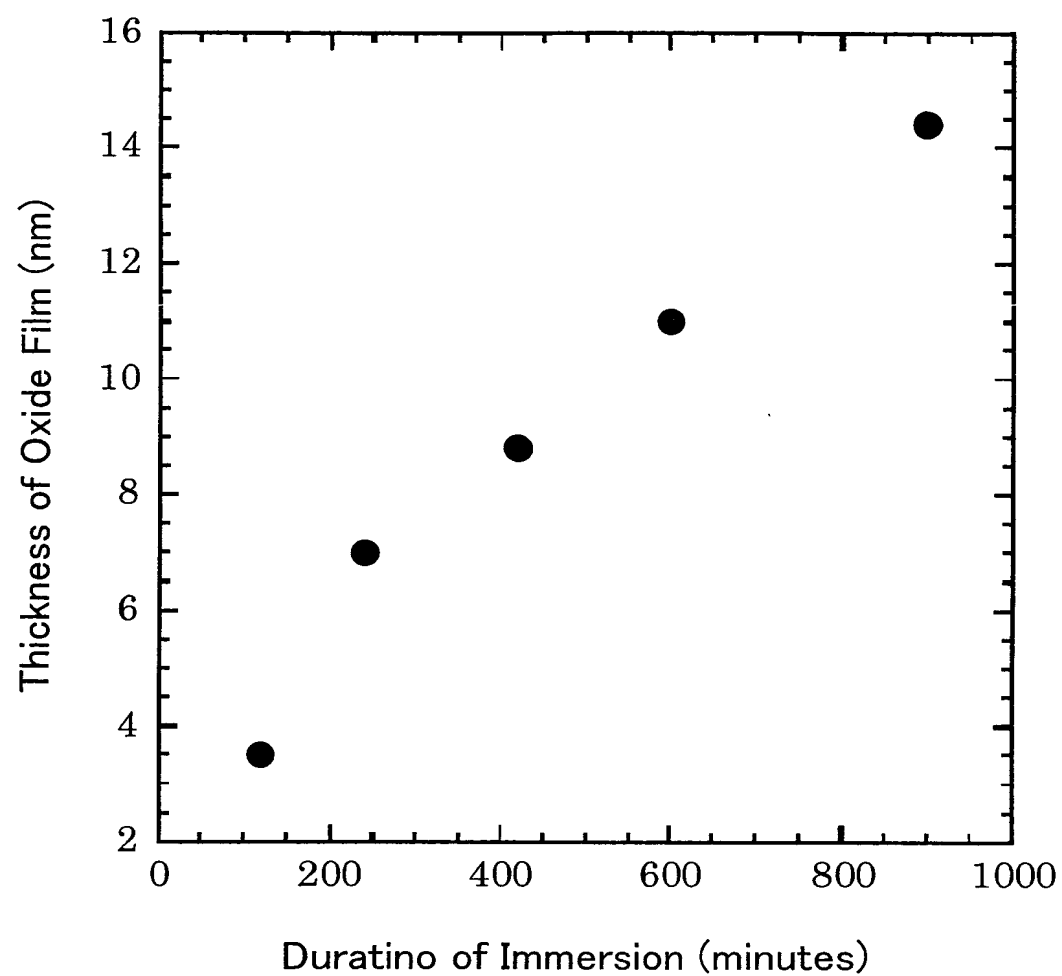


FIG. 29

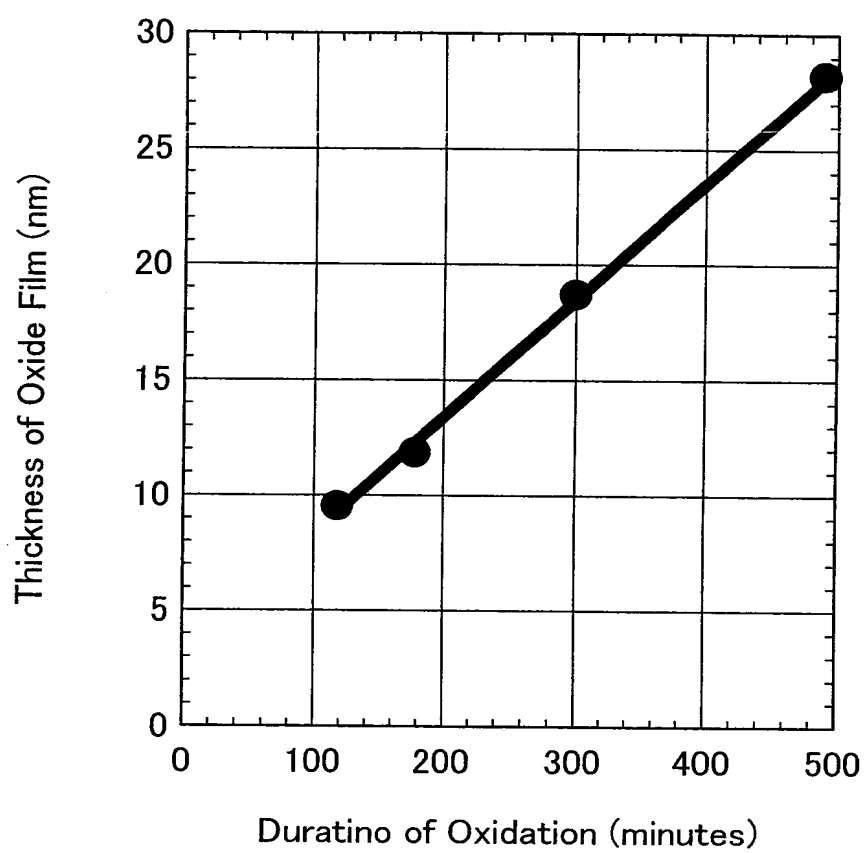


FIG. 30

